

# スパッタ・イオンプレーティング複合人工格子作製装置の開発研究

著者	畑 朋延
著者別表示	Hata Tomonobu
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# 2001 Fiscal Year Final Research Report Summary

## Development Research of Apparatus for Artificial Lattice Utilizing Sputtering and Ion-Plating Combined Technique

Research Project

### Project/Area Number

11555086

### Research Category

Grant-in-Aid for Scientific Research (B)

### Allocation Type

Single-year Grants

### Section

展開研究

### Research Field

Electronic materials/Electric materials

### Research Institution

Kanazawa University

### Principal Investigator

**HATA Tomonobu** Kanazawa University, Faculty of Engineering, Professor, 工学部, 教授 (50019767)

### Co-Investigator(Kenkyū-buntansha)

OKADA Osamu ANELVA Co.Ltd., Head Reseracher, 開発研究所, 所長代理

SASAKI Kimihiro Kanazawa University, Faculty of Engineering, Associate Professor, 工学部, 助教授 (40162359)

### Project Period (FY)

1999 - 2001

### Keywords

Sputtering / Thin Film / Metallic Mode / High-k Material / Limited Reaction / ZrO<sub>2</sub> / MOSFET

### Research Abstract

A new sputtering film deposition method, named Limited Reaction Sputtering Technique, was developed and investigated. Using this technique, ZrO<sub>2</sub> dielectric films were synthesized for gate materials of next generation MOSFETs. The Si substrate surface oxidation was suppressed consequently a high specific dielectric constant as high as over 20 was obtained. On conventional sputtering technique using oxide target, oxygen ions and radicals are easily to be generated, thus Si is oxidized significantly. However, this technique does not generate them, resulting in clear interface between Si substrate and deposited films.

# Research Products (16 results)

All	Other
All	Publications

- [Publications] K.Sasaki et al.: "Limited Reaction Growth of YSZ Thin Films for Gate Insulator"Vacuum. 66. 457-462 (2002) ▼
  
- [Publications] K.Sasaki, T.Hata: "Metallic Mode Growth of ZrO<sub>2</sub>-Based Thin Films for Gate Insulator Using Reactive Sputtering Technique"Ext. Abs. 2001 AWAD. 93-97 (2001) ▼
  
- [Publications] K.Sasaki et al.: "Limited Reaction Growth of YSZ Thin Films for Gate Insulator"Proc. of ISSP. 41-44 (2001) ▼
  
- [Publications] K.Sasaki, H.Hata: "Reactive Growth of YSZ Thin Films with Unpoisoned Sputtering Target"Abs. of Joint Workshop of 29th IUVSAT. 381-389 (2000) ▼
  
- [Publications] T.Hata et al.: "Surface and Interface of Heteroepitaxially Grown YSZ on (100), (110), (111) Si Substrate by Reactive Sputtering"Abs. IJC-Si. PI-29 (1999) ▼
  
- [Publications] M.Nagashima: "Growth Dependence of Reactive Sputtering Yttria-Stabilized Zirconia on Si(100), (110), (111)"Jpn. J. Appl. Phys.. 38. L74-L77 (1999) ▼
  
- [Publications] Kimihiro Sasaki, Tatsuhiro Hasu, Kenji Sasaki, Tomonobu Hata: ""Limited Reaction Growth of YSZ(ZrO<sub>2</sub> : Y<sub>2</sub>O<sub>3</sub>) Thin Films for Gate Insulator"Vacuum. in press. ▼
  
- [Publications] K.Sasaki, T.Hata: "Metallic Mode Growth of ZrO<sub>2</sub>-Based Thin Films for Gate Insulator Using Reactive Sputtering Technique"2001 AWAD. 93-97 (2001) ▼
  
- [Publications] K.Sasaki, T.Hasu, K.Sasaki, T.Hata: "Limited Reaction Growth of YSZ (ZrO<sub>2</sub>:Y<sub>2</sub>O<sub>3</sub>) Thin Films for Gate Insulator"Proc. Of ISSP. 41-44 (2001) ▼
  
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- [Publications] Tomonobu Hata, Kenji Sasaki, Yohko Ichikawa, Kihiro Sasaki: "Yttria-Stabilized Zirconia (YSZ) heteroepitaxially grown on Si substrates by reactive sputtering"Vacuum. Vol.59(2-3). 381-389 (2000) ▼
  
- [Publications] T.Hata K.Sasaki, Y.Ichikawa, M.Nagashima, K.sasaki: "Surface and Interface of Heteroepitaxially Grown Yttria-Stabilized Zirconia (YSZ) on (100), (110), (111) Si Substrates by Reactive Sputtering"Program & Abstracts. IJC-Si. PI-29 (1999) ▼
  
- [Publications] T Hata K Sasaki, Y.Ichikawa, K.Sasaki: "Mechanisms of heteroepitaxial grown Yttria-Stabilized Zirconia (YSZ) on Si substrates by reactive sputtering"Proc. 5th ISSP '99. 1-2 (1999) ▼
  
- [Publications] M.Nagashima, S.Nakano, K.Sasaki, T.Hata: "Growth Dependence of Reactive Sputtered Yttria-Stabilized Zirconia on Si (100), (110), (111) Substrates"Jpn. J. Appl. Phys. 38, Part2, [1A/B]. L74-L77 (1999) ▼
  
- [Publications] K.Kawai, T.Hasu, K.Monju, R.Izumi, K.Sasaki, T.Hata: "Growth of ZrO<sub>2</sub> and Gate Insulation Film Characteristics by Limited-Reaction Sputtering"Tech. Rep. Of IEICE. SDM2002-62. 27-31 (2002) ▼
  
- [Publications] K.Sasaki, T.Hasu, K.Sasaki, T.Hata: "Preparation of YSZ Ultra thin Film for Gate Insulator Films by Metal/Oxide Mode"Tech. Rep. Of IEICE. CPM2000-123. 39-44 (2000) ▼

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